

Supporting Information

$\text{Lu}_2\text{CaMg}_2(\text{Si}_{1-x}\text{Ge}_x)_3\text{O}_{12}$: Ce^{3+} Solid-solution

Phosphors: Bandgap Engineering for Blue-light

Activated Afterglow Applicable to AC-LED

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Table S1. Refinement results of interatomic distances in $\text{Lu}_{1.99}\text{CaMg}_2\text{Si}_{1.5}\text{Ge}_{1.5}\text{O}_{12}$ solid-solution phosphors.

Bonds	Distance (nm)	Bonds	Distance (nm)
$\text{Lu}_1(\text{Ca}_1)\text{-O}_1$	0.2514	$\text{Mg}_1\text{-O}_1$	0.1979
$\text{Lu}_1(\text{Ca}_1)\text{-O}_2$	0.2387	$\text{Si}_1(\text{Ge}_1)\text{-O}_1$	0.1695

Table S2. Estimated thermal quenching parameters of Ce^{3+} -doped LCMSGO solid-solution phosphors.

Sample	$T_{0.5}$ (K)	E_q (eV)
Si:Ge=2:1	360	0.207
Si:Ge=1:1	320	0.188
Si:Ge=1:2	290	0.158
LCMGO	240	0.149

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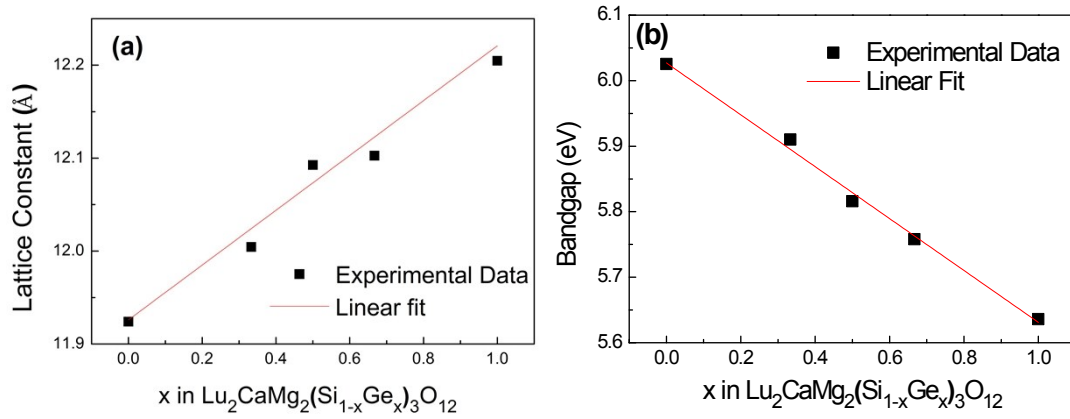


Figure S1. Dependence of the (a) lattice constant and (b) bandgap on x of the compounds $\text{Lu}_2\text{CaMg}_2(\text{Si}_{1-x}\text{Ge}_x)_3\text{O}_{12}$.

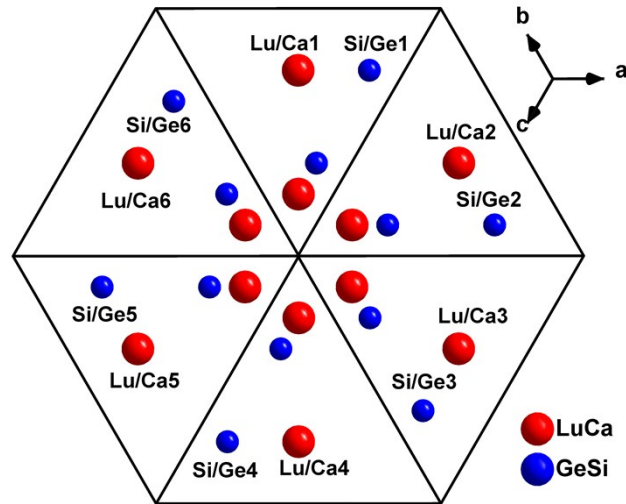


Figure S2. Schematic illustration of the method dealing with the Lu/Ca and Ge/Si cation disorders in DFT calculation. In order to remain the symmetry to the most extent, the Si/Ge1, Si/Ge3, and Si/Ge5 sites were set to be occupied by Si, while the Si/Ge2, Si/Ge4, and Si/Ge6 sites by Ge; likewise, the Ca/Lu1 and Ca/Lu4 sites were set to be occupied by Ca, while the Ca/Lu2, Ca/Lu3, Ca/Lu5, and Ca/Lu6 sites by Lu.

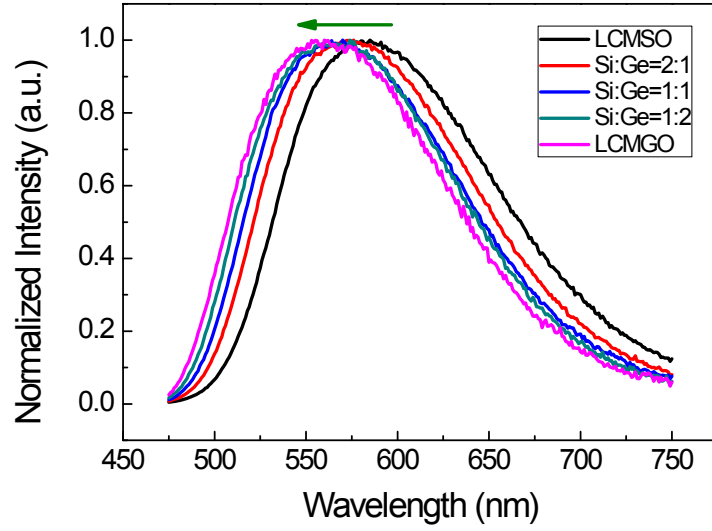


Figure S3. Normalized emission spectra of the $\text{Lu}_2\text{CaMg}_2(\text{Si}_{1-x}\text{Ge}_x)_3\text{O}_{12}:0.01\text{Ce}^{3+}$ ($x=0-1$) samples with various Si:Ge ratio upon 460 nm excitation.

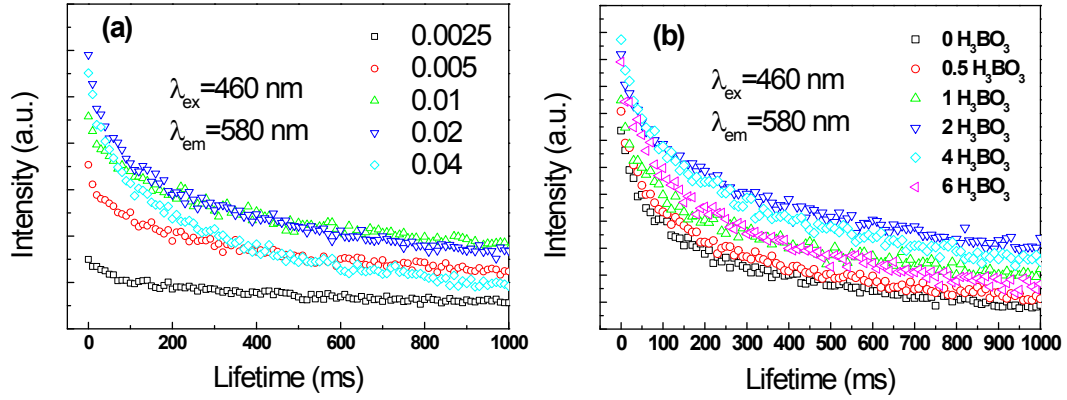


Figure S4. PersL decay curves for (a) the $\text{Lu}_2\text{CaMg}_2(\text{Si}_{1-x}\text{Ge}_x)_3\text{O}_{12}:x\text{Ce}^{3+}$ phosphors ($x=0.005-0.04$) and (b) the $\text{Lu}_2\text{CaMg}_2\text{Si}_{1.5}\text{Ge}_{1.5}\text{O}_{12}:0.01\text{Ce}^{3+}$ phosphors with various the H_3BO_3 amount (0-6 wt%).

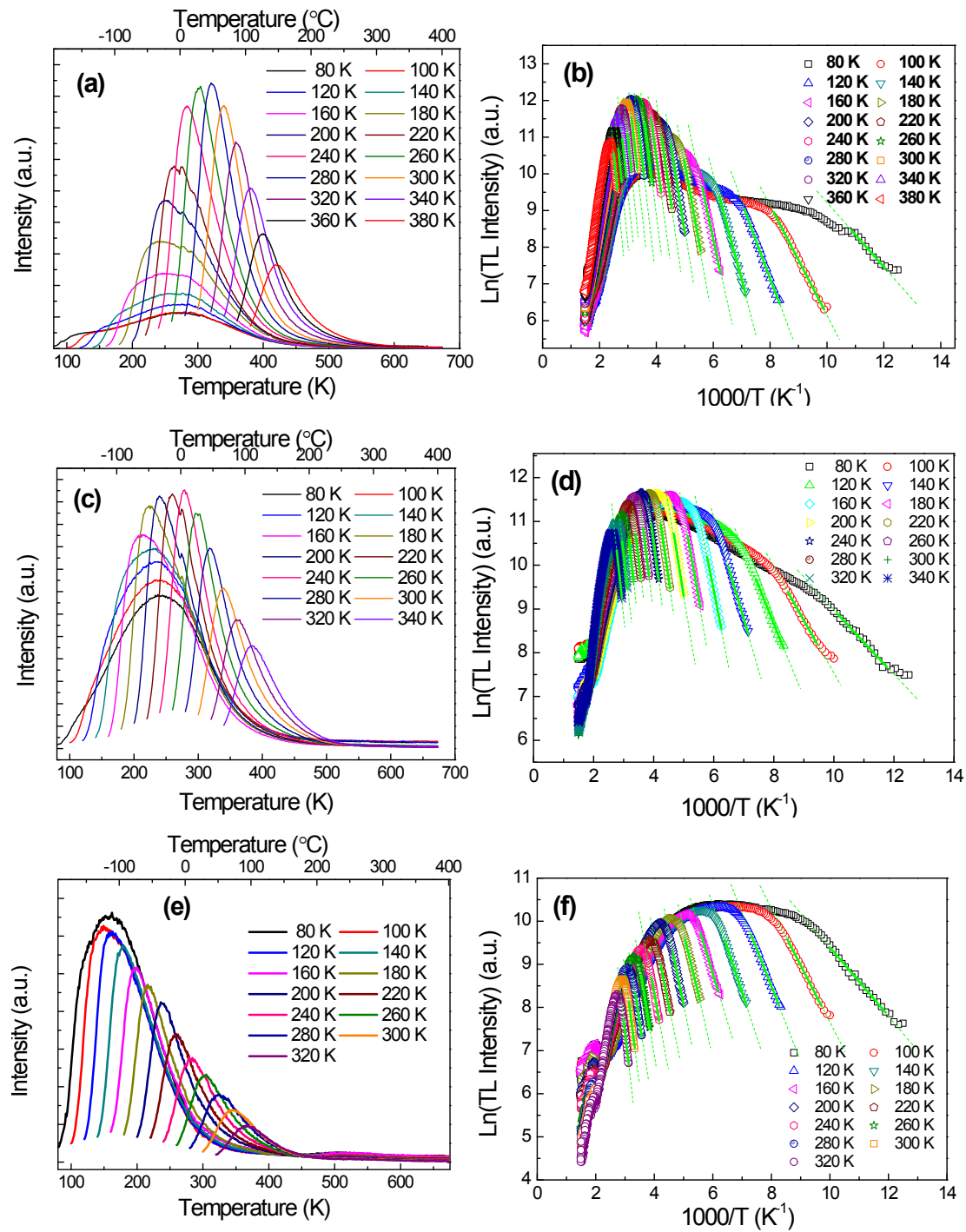


Figure S5. TL curves by pre-heating/cooling the (a) Si:Ge=1:1, (c) Si:Ge=1:2, and (e) LCMGO samples at different T_{exc} (excitation wavelength: 460 nm, heating rate: 1K/s). Corresponding initial rise analyses on the TL curves of (b) Si:Ge=1:1, (d) Si:Ge=1:2, and (f) LCMGO samples as a function of T_{exc} .

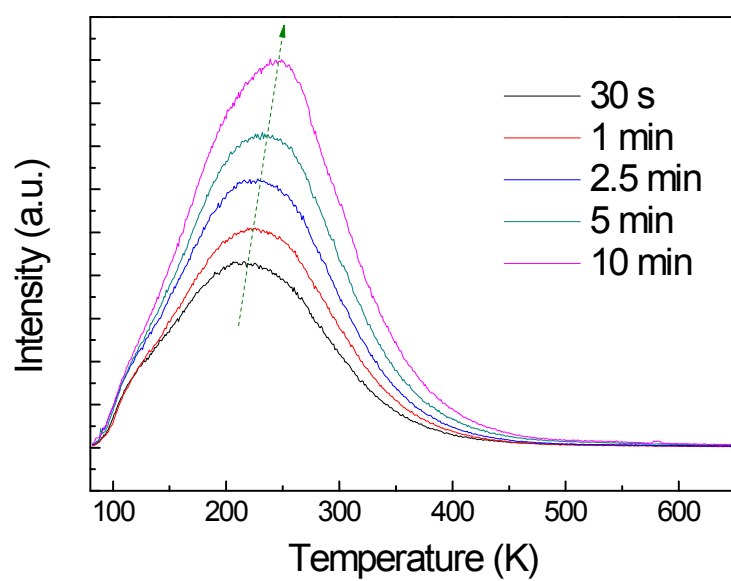


Figure S6. Excitation time dependent TL glow curves of the $\text{Lu}_2\text{CaMg}_2\text{Si}_1\text{Ge}_2\text{O}_{12}:0.01\text{Ce}^{3+}$ at a heating rate of 1 K/s ($\lambda_{\text{ex}}=460$ nm, $\lambda_{\text{em}}=580$ nm).